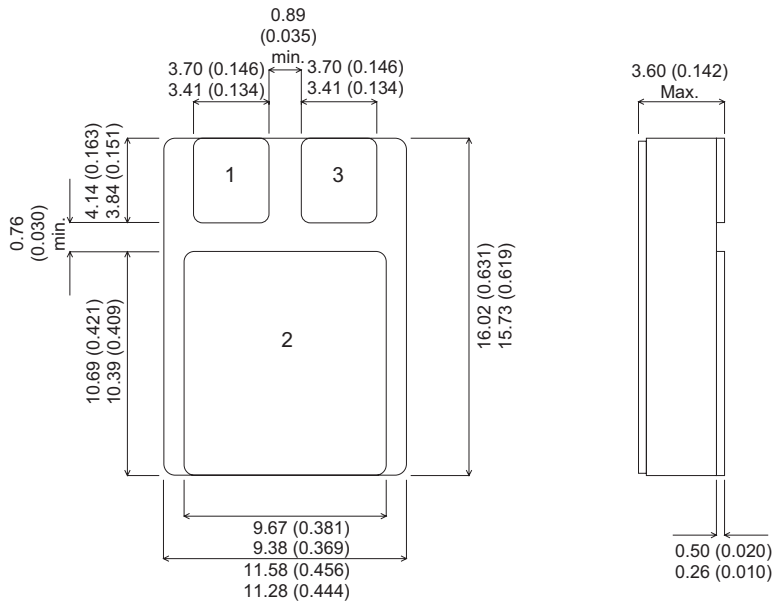


MECHANICAL DATA

Dimensions in mm



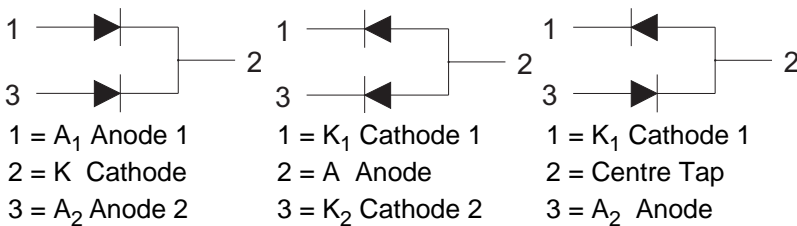
SMD1 Package (TO-276AB)

**DUAL SCHOTTKY
 BARRIER DIODE IN FOR
 HI-REL APPLICATIONS**

FEATURES

- HERMETIC CERAMIC PACKAGE
- ISOLATED CASE
- SCREENING OPTIONS AVAILABLE
- OUTPUT CURRENT 30A
- LOW V_F

Common Cathode SB30-100M Common Anode SB30-100A Series Connection SB30-100R



ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^\circ C$ unless otherwise stated)

V_{RRM}	Peak Repetitive Reverse Voltage (Per Leg)	100V
V_{RSM}	Peak Non-Repetitive Reverse Voltage (Per Leg)	100V
V_R	Continuous Reverse Voltage (Per Leg)	100V
$I_{F(AV)}$	Maximum Average Forward Current	30A
I_{FSM}^*	Peak Non-Repetitive Surge Current (per leg)	100A
T_{STG}	Storage Temperature Range	-55°C to 150°C
T_J	Maximum Operating Junction Temperature	150°C

* $t_p = 8.3ms$ half-sine

ELECTRICAL CHARACTERISTICS ($T_{CASE} = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F Maximum Forward Voltage Drop (per diode)*	$I_F = 15A$ $T_J = 25^{\circ}C$			1.03	V
	$I_F = 30A$ $T_J = 25^{\circ}C$			1.27	
	$I_F = 15A$ $T_J = 125^{\circ}C$			0.77	
	$I_F = 30A$ $T_J = 125^{\circ}C$			0.95	
I_R Reverse Maximum Leakage Current (per diode)*	$V_R = 100V$ $T_J = 25^{\circ}C$			0.55	mA
	$V_R = 100V$ $T_J = 125^{\circ}C$			9.0	
C_T Junction Capacitance (per diode)	$V_R = 5 V$ $f = 1 MHz$		215		pF

*Pulse test $t_p=300\mu s$ $\delta \leq 2\%$

Parameter	Unit
$R_{TH(j-c)}$ Maximum Thermal Resistance Junction To Case (per package)	1.3 °C/W
$R_{TH(j-c)}$ Maximum Thermal Resistance Junction To Case (per diode)	2.4 °C/W